

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A lapping polishing-agent used for lapping a silicon wafer, containing at least silica powder that is produced by melting raw material silica powder in a flame and is substantially spherical or perfectly spherical and alumina powder, wherein the average grain diameter of the silica powder is 2-7 μm .
2. (Currently Amended) The lapping polishing-agent according to claim 1, wherein the average grain diameter of the silica powder is smaller than the average grain diameter of the alumina powder.
3. - 4. (Canceled)
5. (Currently Amended) The lapping polishing-agent according to claim 1, wherein the amount of the silica contained in the polishing agent is 20-50 percent by weight.
6. (Currently Amended) The lapping polishing-agent according to claim 2, wherein the amount of the silica contained in the polishing agent is 20-50 percent by weight.
7. - 8. (Canceled)
9. (Currently Amended) A lapping method comprising introducing a lapping the polishing-agent according to claim 1 to a workpiece silicon wafer, wherein the lapping agent contains at least silica powder that is produced by melting raw material silica powder in a flame and is substantially spherical or perfectly spherical and alumina powder, wherein the average grain diameter of the silica powder is 2-7 μm , and lapping the silicon wafer workpiece in the presence of the lapping polishing-agent.
10. (Currently Amended) The A-lapping method according to claim 9, wherein the average grain diameter of the silica powder is smaller than the average grain diameter of

~~the alumina powder comprising introducing the polishing agent according to claim 2 to a workpiece, and lapping the workpiece in the presence of the polishing agent.~~

11. - 12. (Canceled)

13. (Currently Amended) The A-lapping method according to claim 9, wherein the amount of the silica contained in the lapping agent is 20-50 percent by weight comprising introducing the polishing agent according to claim 5 to a workpiece, and lapping the workpiece in the presence of the polishing agent.

14. (Currently Amended) The A-lapping method according to claim 10, wherein the amount of the silica contained in the lapping agent is 20-50 percent by weight comprising introducing the polishing agent according to claim 6 to a workpiece, and lapping the workpiece in the presence of the polishing agent.

15. - 16. (Canceled)

17. (Currently Amended) A lapping method in which a silicon wafer workpiece is held between an upper turn table and a lower turn table, the silicon wafer workpiece being lapped by rotating the upper and the lower turn tables while being supplied with a lapping polishing agent, wherein the lapping polishing agent is a lapping polishing agent containing at least silica powder that is produced by melting raw material silica powder in a flame and is substantially spherical or perfectly spherical and alumina powder, and wherein the average grain diameter of the silica powder is 2-7 μm .

18. - 19. (Canceled)